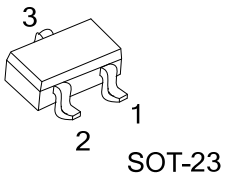
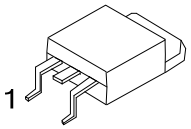
N-CHANNEL ENHANCEMENT MODE POWER MOSFET



SOT-23
(EIAJ SC-59)



TO-252

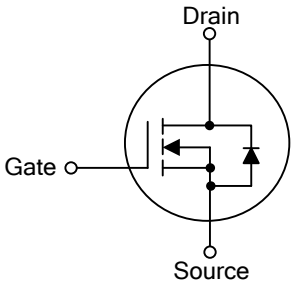
■ DESCRIPTION

The UTC **UT3N06** is an N-channel power MOSFET providing very low on-resistance. It has high efficiency and perfect cost-effectiveness. It can be generally applied in the commercial and industrial fields.

■ FEATURES

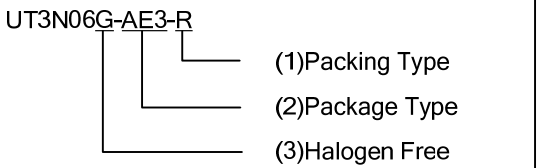
* Simple drive requirement

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT3N06L-AE3-R	UT3N06G-AE3-R	SOT-23	S	G	D	Tape Reel
UT3N06L-TN3-R	UT3N06G-TN3-R	TO-252	G	D	S	Tape Reel
UT3N06L-TN3-T	UT3N06G-TN3-T	TO-252	G	D	S	Tube

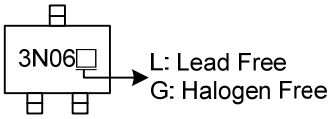


(1) R: Tape Reel

(2) AE3: SOT-23, TN3: TO-252

(3) G: Halogen Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (V_{GS}=4.5V, T_A= 25°C) (Note 2)		I_D	3.0	A
Pulsed Drain Current (Note 3, 4)		I_{DM}	10	A
Power Dissipation (T_A= 25°C)	SOT-23	P_D	0.35	W
	TO-252		1.13	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Surface mounted on 1 in^2 copper pad of FR4 board; 270°C/W when mounted on min. copper pad.
3. Pulse width limited by $T_{J(MAX)}$
4. Pulse width ≤300μs, duty cycle≤2%.

■ THERMAL DATA

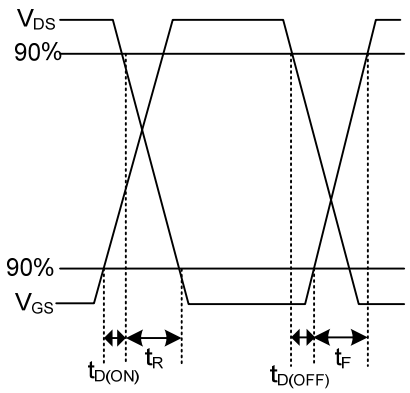
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	SOT-23	θ_{JA}	350	°C/W
	TO-252		110	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

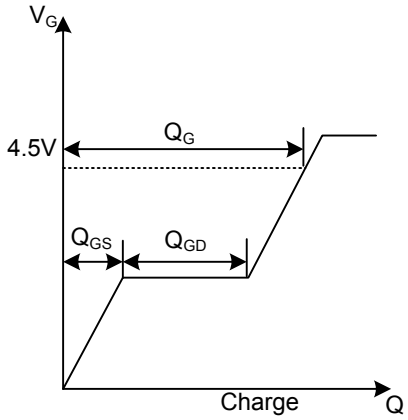
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250μA	60			V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Reference to 25°C, I_D=1mA		0.05		V/°C
Drain-Source Leakage Current	I_{DSS}	V_{DS} =60V,V_{GS} =0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS} =V_{GS}, I_D =250μA	1.0		3.0	V
Drain to Source On-state Resistance	$R_{DS(ON)}$	V_{GS} =10V, I_D =3A			90	mΩ
		V_{GS} =4.5V, I_D =2A			120	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{DS}=25V,V_{GS}=0V,f =1.0MHz		490	780	pF
Output Capacitance	C_{OSS}			55		pF
Reverse Transfer Capacitance	C_{RSS}			40		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time (Note)	$t_{D(ON)}$	V_{GS}=10V, V_{DS}=30V, I_D=1A, R_D =30Ω, R_G =3.3Ω		6		ns
Turn-ON Rise Time	t_R			5	42	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			16		ns
Turn-OFF Fall-Time	t_F			3	58	ns
Total Gate Charge (Note)	Q_G	V_{GS} =4.5V, V_{DS} =48V, I_D =3A		6	10	nC
Gate Source Charge	Q_{GS}			1.6		nC
Gate Drain Charge	Q_{GD}			3		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage (Note)	V_{SD}	I_S =1.2A, V_{GS} =0V			1.2	V
Reverse Recovery Time	t_{rr}	I_S=3A,V_{GS}=0V, dI/dt=100A/μs		25		ns
Reverse Recovery Charge	Q_{RR}			26		nC

Note: Pulse width ≤300μs, duty cycle≤2%.

■ TEST WAVEFORMS



Switching Time Waveform



Gate Charge Waveform